



TUSB2046x 4-Port Hub for the Universal Serial Bus With Optional Serial EEPROM Interface

1 Features

- Fully Compliant With the USB Specification as a Full-Speed Hub: TID #30220231
- 32-Pin LQFP ⁽¹⁾ Package With a 0.8-mm Terminal Pitch or QFN Package With a 0.5-mm Pin Pitch
- 3.3-V Low-Power ASIC Logic
- Integrated USB Transceivers
- State Machine Implementation Requires No Firmware Programming
- One Upstream Port and Four Downstream Ports
- All Downstream Ports Support Full-Speed and Low-Speed Operations
- Two Power Source Modes
 - Self-Powered Mode
 - Bus-Powered Mode
- Power Switching and Overcurrent Reporting Is Provided Ganged or Per Port
- Supports Suspend and Resume Operations
- Supports Programmable Vendor ID and Product ID With External Serial EEPROM
- 3-State EEPROM Interface Allows EEPROM Sharing
- Push-Pull Outputs for PWRON Eliminate the Need for External Pullup Resistors
- Noise Filtering on OVRCUR Provides Immunity to Voltage Spikes
- Package Pinout Allows 2-Layer PCB
- Low EMI Emission Achieved by a 6-MHz Crystal Input
- Migrated From Proven TUSB2040 Hub
- Lower Cost Than the TUSB2040 Hub
- Enhanced System ESD Performance
- No Special Driver Requirements; Works Seamlessly With Any Operating System With USB Stack Support
- Supports 6-MHz Operation Through a Crystal Input or a 48-MHz Input Clock

(1) JEDEC descriptor S-PQFP-G for low-profile quad flatpack (LQFP).

2 Applications

- Computer Systems
- Docking Stations

3 Description

The TUSB2046x is a 3.3-V CMOS hub device that provides one upstream port and four downstream ports in compliance with the Universal Serial Bus (USB) specification as a full-speed hub. Because this device is implemented with a digital state machine instead of a microcontroller, no firmware programming is required. Fully compliant USB transceivers are integrated into the ASIC for all upstream and downstream ports. The downstream ports support full-speed and low-speed devices by automatically setting the slew rate according to the speed of the device attached to the ports. The configuration of the BUSPWR pin selects either the bus-powered or the self-powered mode.

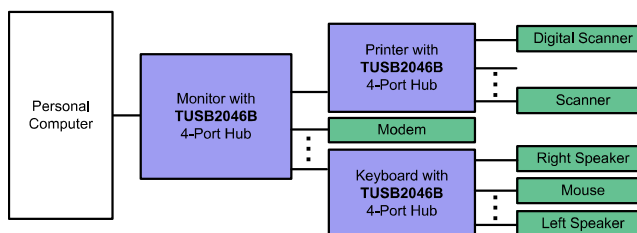
Configuring the GANGED input determines the power switching and overcurrent detection modes for the downstream ports. If GANGED is high, all PWRON outputs switch together and if any OVRCUR is activated, all ports transition to the power-off state. If GANGED is low, the PWRON outputs and OVRCUR inputs operate on a per-port basis.

Device Information⁽¹⁾

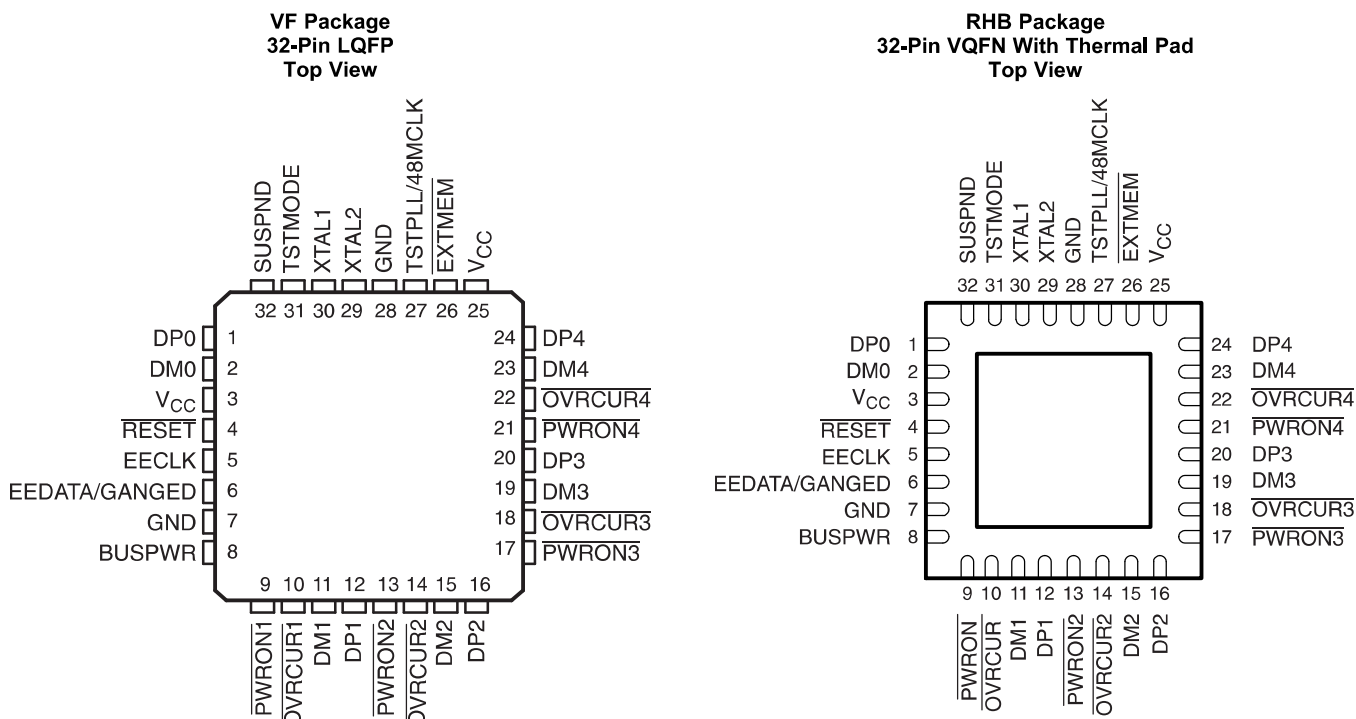
PART NUMBER	PACKAGE	BODY SIZE (NOM)
TUSB2046B	VQFN (32)	5.00 mm × 5.00 mm
TUSB2046BI	LQFP (32)	7.00 mm × 7.00 mm
TUSB2046I		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

USB-Tiered Configuration Example



6 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
BUSPWR	8	I	Power source indicator. BUSPWR is an active-high input that indicates whether the downstream ports source their power from the USB cable or a local power supply. For the bus-power mode, this terminal must be pulled to 3.3 V, and for the self-powered mode, this terminal must be pulled low. Input must not change dynamically during operation.
DM0	2	I/O	Root port USB differential data minus. DM0 paired with DP0 constitutes the upstream USB port.
DM1	11		
DM2	15		
DM3	19		
DM4	23	I/O	USB differential data minus. DM1–DM4 paired with DP1–DP4 support up to four downstream USB ports.
DP0	1		
DP1	12		
DP2	16		
DP3	20		
DP4	24		
EECLK	5	O	EEPROM serial clock. When $\overline{\text{EXTMEM}}$ is high, the EEPROM interface is disabled. The EECLK terminal is disabled and must be left floating (unconnected). When $\overline{\text{EXTMEM}}$ is low, EECLK acts as a 3-state serial clock output to the EEPROM with a 100- μ A internal pulldown.
EEDATA/GANGED	6	I/O	EEPROM serial data/power-management mode indicator. When $\overline{\text{EXTMEM}}$ is high, EEDATA/GANGED selects between ganged or per-port power overcurrent detection for the downstream ports. When $\overline{\text{EXTMEM}}$ is low, EEDATA/GANGED acts as a serial data I/O for the EEPROM and is internally pulled down with a 100- μ A pulldown. This standard TTL input must not change dynamically during operation.
$\overline{\text{EXTMEM}}$	26	I	When $\overline{\text{EXTMEM}}$ is high, the serial EEPROM interface of the device is disabled. When $\overline{\text{EXTMEM}}$ is low, terminals 5 and 6 are configured as the clock and data terminals of the serial EEPROM interface, respectively.
GND	7, 28		GND terminals must be tied to ground for proper operation.

7 Specifications

7.1 Absolute Maximum Ratings

 over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾		−0.5	3.6	V
V _I	Input voltage range		−0.5	V _{CC} + 0.5	V
V _O	Output voltage range		−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0 V or V _I < V _{CC}	±20		mA
I _{OK}	Output clamp current	V _O < 0 V or V _O < V _{CC}	±20		mA
T _A	Operating free-air temperature	TUSB2046B	0	70	°C
		TUSB2046BI, TUSB2046I	−40	85	
T _{stg}	Storage temperature range		−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage levels are with respect to GND.

7.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

PARAMETER		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	TUSB2046B		3	V
		TUSB2046BI, TUSB2046I		3.3	
V _I	Input voltage, TTL/LVCMOS	0		V _{CC}	V
V _O	Output voltage, TTL/LVCMOS	0		V _{CC}	V
V _{IH(REC)}	High-level input voltage, signal-ended receiver	2		V _{CC}	V
V _{IL(REC)}	Low-level input voltage, signal-ended receiver			0.8	V
V _{IH(TTL)}	High-level input voltage, TTL/LVCMOS	2		V _{CC}	V
V _{IL(TTL)}	Low-level input voltage, TTL/LVCMOS	0		0.8	V
T _A	Operating free-air temperature	TUSB2046B		0	°C
		TUSB2046BI, TUSB2046I		−40	
R _(DRV)	External series, differential driver resistor	22 (−5%)		22 (5%)	Ω
f _(OPRH)	Operating (dc differential driver) high speed mode			12	Mb/s
f _(OPRL)	Operating (dc differential driver) low speed mode			1.5	Mb/s
V _{ICR}	Common mode, input range, differential receiver	0.8		2.5	V
t _t	Input transition times, TTL/LVCMOS	0		25	ns
T _J	Junction temperature range	−40		115	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TUSB2046x	UNIT
		RHB (VQFN)	
		32 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	35.7	°C/W
R _{θJCTop}	Junction-to-case (top) thermal resistance	28.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	9.9	°C/W
ψ _{JT}	Junction-to-top characterization parameter	0.5	°C/W
ψ _{JB}	Junction-to-board characterization parameter	9.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	4.3	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics

over recommended ranges of operating free-air temperature and supply voltage (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
V _{OH}	High-level output voltage	TTL/LVCMOS	I _{OH} = −4 mA	V _{CC} − 0.5	V
		USB data lines	R _(DRV) = 15 kΩ to GND	2.8	
			I _{OH} = −12 mA (without R _(DRV))	V _{CC} − 0.5	
V _{OL}	Low-level output voltage	TTL/LVCMOS	I _{OL} = 4 mA	0.5	V
		USB data lines	R _(DRV) = 1.5 kΩ to 3.6 V	0.3	
			I _{OL} = 12 mA (without R _(DRV))	0.5	
V _{IT+}	Positive input threshold	TTL/LVCMOS		1.8	V
		Single-ended	0.8 V ≤ V _{ICR} ≤ 2.5 V	1.8	
V _{IT−}	Negative-input threshold	TTL/LVCMOS		0.8	V
		Single-ended	0.8 V ≤ V _{ICR} ≤ 2.5 V	1	
V _{hys}	Input hysteresis ⁽¹⁾ (V _{T+} − V _{T−})	TTL/LVCMOS		0.3	mV
		Single-ended	0.8 V ≤ V _{ICR} ≤ 2.5 V	300	
I _{OZ}	High-impedance output current	TTL/LVCMOS	V = V _{CC} or GND ⁽²⁾	±10	μA
		USB data lines	0 V ≤ V _O ≤ V _{CC}	±10	
I _{IL}	Low-level input current	TTL/LVCMOS	V _I = GND	−1	μA
I _{IH}	High-level input current	TTL/LVCMOS	V _I = V _{CC}	1	μA
Z _{0(DRV)}	Driver output impedance	USB data lines	Static V _{OH} or V _{OL}	7.1	19.9 Ω
V _{ID}	Differential input voltage	USB data lines	0.8 V ≤ V _{ICR} ≤ 2.5 V	0.2	V
I _{CC}	Input supply current		Normal operation	40	mA
			Suspend mode	1	μA

(1) Applies for input buffers with hysteresis.

(2) Applies for open-drain buffers.

7.6 Differential Driver Switching Characteristics (Full Speed Mode)

over recommended ranges of operating free-air temperature and supply voltage, C_L = 50 pF (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
t _r	Transition rise time for DP or DM	See Figure 1 and Figure 2	4	20	ns
t _f	Transition fall time for DP or DM	See Figure 1 and Figure 2	4	20	ns
t _(RFM)	Rise/fall time matching ⁽¹⁾	(t _r /t _f) × 100	90%	110%	
V _{O(CRS)}	Signal crossover output voltage ⁽¹⁾		1.3	2.0	V

(1) Characterized only. Limits are approved by design and are not production tested.

7.7 Differential Driver Switching Characteristics (Low Speed Mode)

over recommended ranges of operating free-air temperature and supply voltage, $C_L = 50$ pF (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
t_r Transition rise time for DP or DM ⁽¹⁾	$C_L = 200$ pF to 600 pF, See Figure 1 and Figure 2	75	300	ns
t_f Transition fall time for DP or DM ⁽¹⁾	$C_L = 200$ pF to 600 pF, See Figure 1 and Figure 2	75	300	ns
$t_{(RFM)}$ Rise/fall time matching ⁽¹⁾	$(t_r/t_f) \times 100$	80%	120%	
$V_{O(CRS)}$ Signal crossover output voltage ⁽¹⁾	$C_L = 200$ pF to 600 pF	1.3	2.0	V

(1) Characterized only. Limits are approved by design and are not production tested.

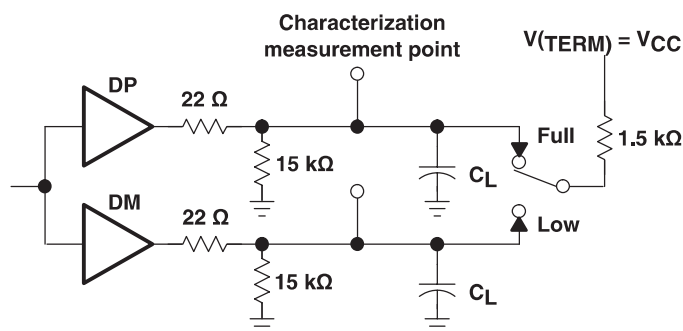
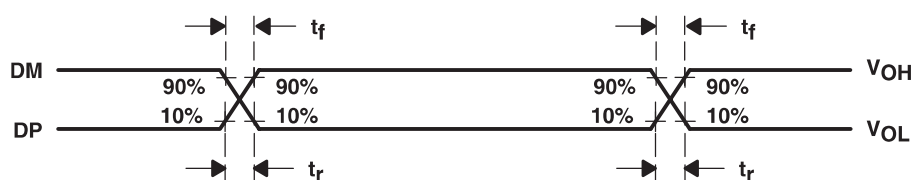


Figure 1. Differential Driver Switching Load



NOTE: The t_r/t_f ratio is measured as $t_r(DP)/t_f(DM)$ and $t_r(DM)/t_f(DP)$ at each crossover point.

Figure 2. Differential Driver Timing Waveforms

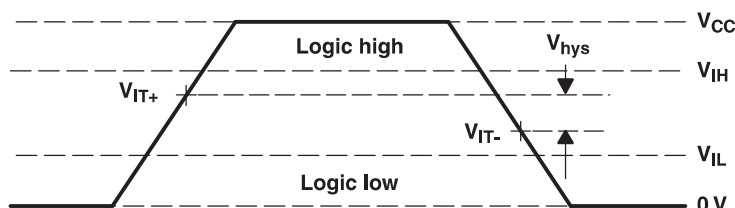


Figure 3. Single-Ended Receiver Input Signal Parameter Definitions

